

INCHANGE SEMICONDUCTOR

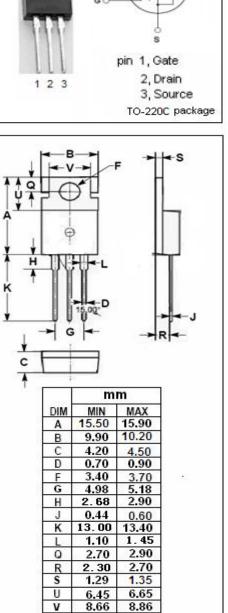
isc N-Channel MOSFET Transistor

IXTP200N055T2

P

RDS(• Fully cl • 100% a • Minimu perforn • APPLIA • DC/DC • High C	drain-source on-resistance: on) $\leq 4.2m\Omega@V_{GS}=10V$ naracterized avalanche voltage and avalanche tested im Lot-to-Lot variations for robust de nance and reliable operation	pin 1, 1 2 3 TO-22		
SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	55	V	
V _{GS}	Gate-Source Voltage	±20	V	15,00 ^{-D}
ID	Drain Current-Continuous	200	А	
I _{DM}	Drain Current-Single Pulsed	500	А	
P _D	Total Dissipation @T _c =25℃	360	W	DIM MIN MAX A 15.50 15.90
Tj	Operating Junction Temperature	-55~175	°C	B 9.90 10.20 C 4.20 4.50 D 0.70 0.90
T _{stg}	Storage Temperature	-55~175	°C	F 3.40 3.70 G 4.98 5.18 H 2.68 2.90
• THERM	IAL CHARACTERISTICS			J 0.44 0.60 K 13.00 13.40 L 1.10 1.45

SYMBOL	PARAMETER	МАХ	UNIT
R _{th(j-c)}	Junction-to-case thermal resistance	0.42	°C/W





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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID = 250 μ A	55		V	
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID = 250 μ A	2.0	4.0	V	
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D = 50A		4.2	mΩ	
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} =0V		±200	nA	
I _{DSS}	Drain-Source Leakage Current	V _{DS} = V _{DSS} ; V _{GS} = 0V		5	- μΑ	
		V _{DS} = V _{DSS} ; V _{GS} = 0V;T _J = 150°C		50		
V _{SD}	Diode forward voltage	I _F = 50A; V _{GS} = 0V		1.1	V	

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